


Cite this: *RSC Adv.*, 2024, 14, 35559

DOI: 10.1039/d4ra90131b

rsc.li/rsc-advances

## Correction: Improved isoprene detection performance of Si-doped WO<sub>3</sub> films deposited by sputtering and post-annealing

Pin-Kuan Lin,<sup>a</sup> Yi Qin,<sup>a</sup> Xiaoding Qi<sup>\*ab</sup> and Liji Huang<sup>c</sup>

Correction for 'Improved isoprene detection performance of Si-doped WO<sub>3</sub> films deposited by sputtering and post-annealing' by Pin-Kuan Lin *et al.*, *RSC Adv.*, 2024, 14, 13618–13627, <https://doi.org/10.1039/D4RA00184B>.

The authors regret an error in Fig. 1 where Fig. 1b was mistakenly replaced by another image used as a scaling reference.

The corrected Fig. 1, with the original data for Fig. 1b, is shown below.

An independent expert has viewed the new data and has concluded that it is consistent with the discussions and conclusions presented.

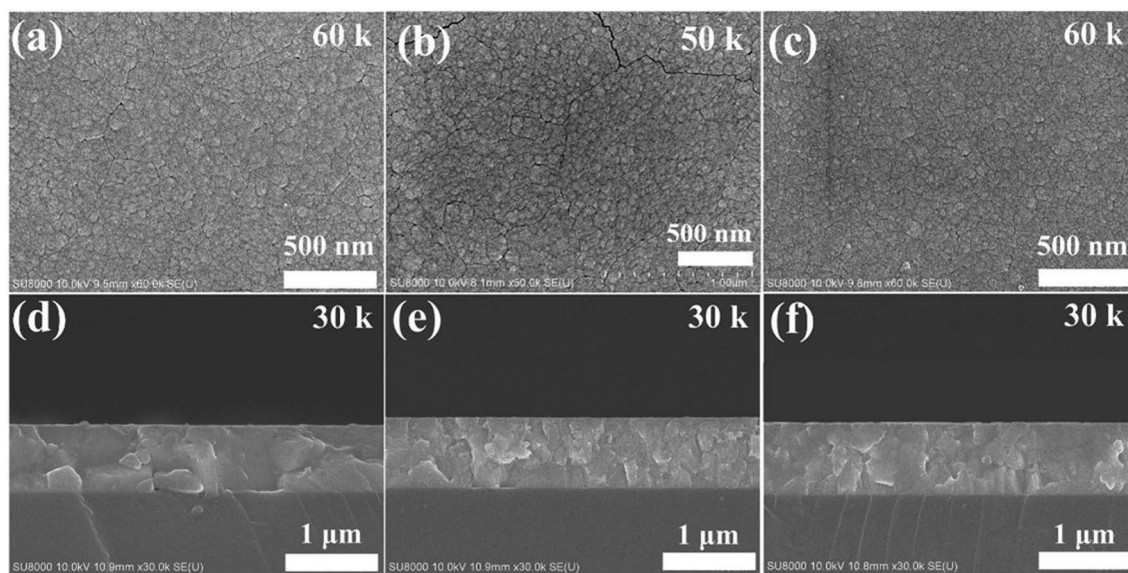


Fig. 1 Surface SEM images for (a) 0SiW, (b) 6SiW and (c) 11SiW. Cross-sectional SEM images for (d) 0SiW, (e) 6SiW and (f) 11SiW.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup>Department of Materials Science and Engineering, National Cheng Kung University, Tainan City 70101, Taiwan. E-mail: xqi045@ncku.edu.tw

<sup>b</sup>Centre for Micro/Nano Science and Technology, National Cheng Kung University, Tainan City 70101, Taiwan

<sup>c</sup>Siargo Ltd, Santa Clara, California 95054, USA

